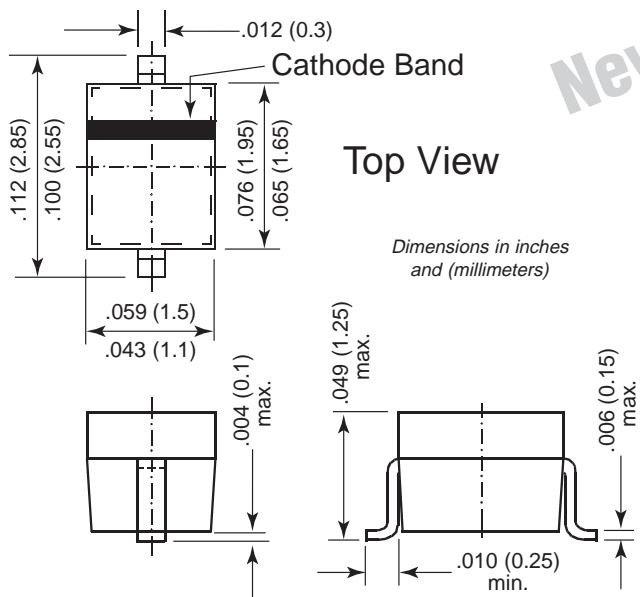
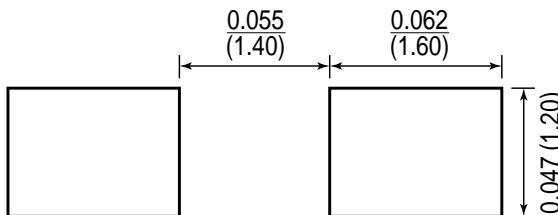




SOD-323



Pad Layout SOD-323



## Features

- Low turn-on voltage
- Fast switching
- Microminiature plastic package
- This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharge.
- Ideal for protection of MOS devices, steering, biasing, and coupling diodes for fast switching and low logic level applications.

## Mechanical Data

**Case:** SOD-323 plastic package

**Weight:** approximately 0.004g

**Marking Code:** SD

**Packaging Codes/Options:**

D5/10K per 13" reel (8mm tape)  
D6/3K per 7" reel (8mm tape)

## Maximum Ratings and Thermal Characteristics (T<sub>C</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Continuous Reverse Voltage	V <sub>R</sub>	30	V
Forward Current	I <sub>F</sub>	200	mA
Forward Surge Current, t <sub>p</sub> = 10 ms	I <sub>FSM</sub>	2	A
Power Dissipation T <sub>C</sub> = 25°C	P <sub>tot</sub>	150	mW
Thermal Resistance Junction to Ambient Air	R <sub>θJA</sub>	650	°C/W
Junction Temperature	T <sub>J</sub>	125	°C
Storage Temperature Range	T <sub>S</sub>	-55 to +150	°C

**Note:** (1) Valid provided that electrodes are kept at ambient temperature

## Electrical Characteristics (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	BV <sub>R</sub>	I <sub>R</sub> = 100 µA	30	—	—	V
Leakage Current	I <sub>R</sub>	V <sub>R</sub> = 30 V	—	—	5.0	µA
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 15 mA	—	320	350	mV
		I <sub>F</sub> = 50 mA	—	370	400	
		I <sub>F</sub> = 150 mA	—	440	460	
		I <sub>F</sub> = 200 mA	—	470	500	
Junction Capacitance	C <sub>tot</sub>	V <sub>R</sub> = 1 V, f = 1.0 MHz	—	25	30	pF